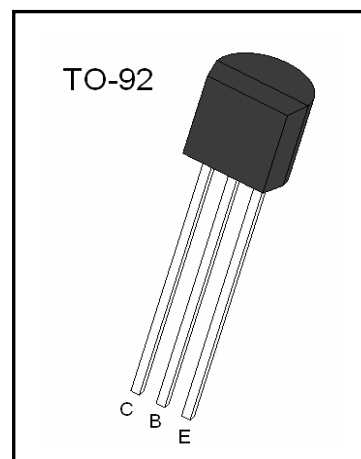


Switching and Applications

- Complement to BC557

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	BV_{CBO}	50	V
Collector-Emitter Voltage	BV_{CEO}	45	V
Emitter-Base Voltage	BV_{EBO}	6	V
Collector Current	I_C	100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature Storage Temperature	T_j , T_{stg}	150 -55~+150	°C



Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-base breakdown voltage	BV_{CBO}	$I_C = 100\mu A$, $I_E = 0$	50			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = 1mA$, $I_B = 0$	45			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = 100\mu A$, $I_C = 0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB} = 45V$, $I_E = 0$			100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V$, $I_C = 0$			100	nA
DC current gain	h_{FE}	$V_{CE} = 5V$, $I_C = 2mA$	110		800	
Collector-emitter saturation voltage	V_{CESAT}	$I_C = 10mA$, $I_B = 0.5mA$ $I_C = 100mA$, $I_B = 5mA$			0.25 0.60	V
base -emitter saturation voltage	V_{BESAT}	$I_C = 100mA$, $I_B = 5mA$			1.0	V
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$			6	pF
Transition frequency	f_T	$V_{CE} = 5V$, $I_B = 10mA$		200		MHz

hFE Classification

Classification	A	B	C
h_{FE}	110-220	200-450	420-800